# **JFET Transistor**

# **N-Channel**

### **Features**

 These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	25	Vdc
Gate-Source Voltage	V <sub>GS</sub>	25	Vdc
Gate Current	I <sub>G</sub>	10	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL CHARACTERISTICS

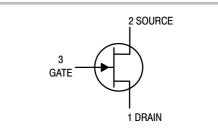
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.



## ON Semiconductor®

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SOT-23 (TO-236AB) CASE 318-08 STYLE 10

### **MARKING DIAGRAM**



M6C = Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
MMBFU310LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1	•	
Gate-Source Breakdown Voltage - (I <sub>G</sub> = -1.0 μAdc, V <sub>DS</sub> = 0)	V <sub>(BR)GSS</sub>	-25	-	Vdc
Gate 1 Leakage Current – (V <sub>GS</sub> = –15 Vdc, V <sub>DS</sub> = 0)	I <sub>G1SS</sub>	-	- 150	pА
Gate 2 Leakage Current – (V <sub>GS</sub> = –15 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 125°C)	I <sub>G2SS</sub>	-	- 150	nAdc
Gate Source Cutoff Voltage – (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 1.0 nAdc)	V <sub>GS(off)</sub>	-2.5	-6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current - (V <sub>DS</sub> = 10 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	24	60	mAdc
Gate-Source Forward Voltage - (I <sub>G</sub> = 10 mAdc, V <sub>DS</sub> = 0)	V <sub>GS(f)</sub>	-	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance – (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 10 mAdc, f = 1.0 kHz)	Y <sub>fs</sub>	10	18	mmhos
Output Admittance - (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 10 mAdc, f = 1.0 kHz)	y <sub>os</sub>	-	250	μmhos
Input Capacitance – (V <sub>GS</sub> = –10 Vdc, V <sub>DS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>iss</sub>	-	5.0	pF
Reverse Transfer Capacitance – (V <sub>GS</sub> = –10 Vdc, V <sub>DS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>rss</sub>	-	2.5	pF

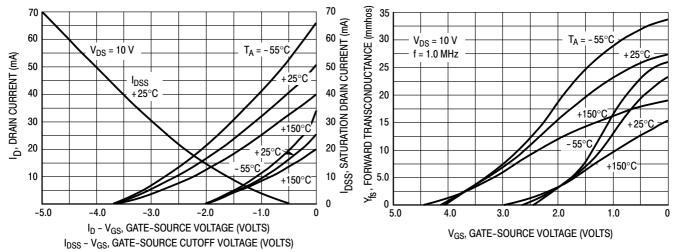


Figure 1. Drain Current and Transfer Characteristics vs Gate-Source Voltage

Figure 2. Forward Transconductance vs Gate-Source Voltage

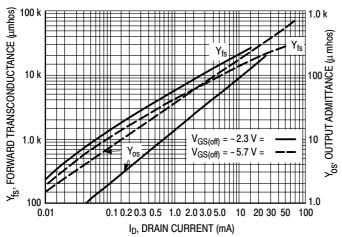


Figure 3. Common-Source Output Admittance and Forward Transconductance vs Drain Current

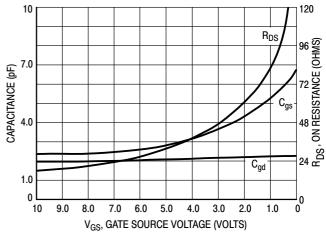


Figure 4. On Resistance and Junction Capacitance vs Gate-Source Voltage

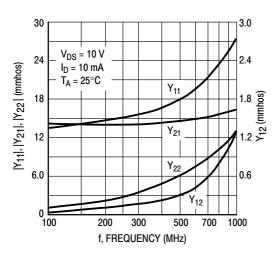


Figure 5. Common-Gate Y Parameter Magnitude vs Frequency

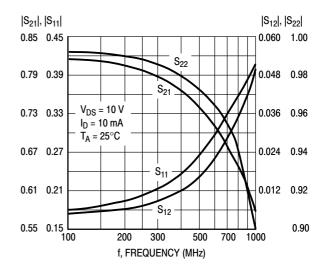


Figure 6. Common-Gate S Parameter Magnitude vs Frequency

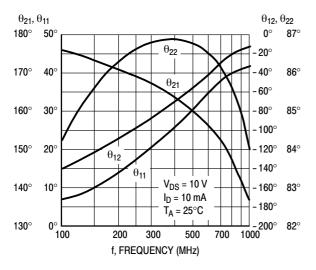


Figure 7. Common-Gate Y Parameter Phase-Angle vs Frequency

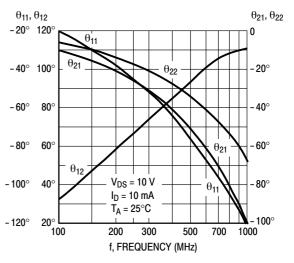
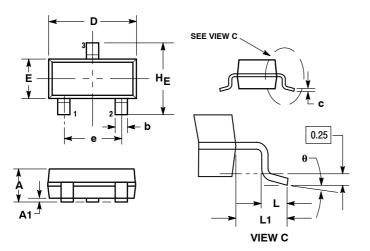


Figure 8. S Parameter Phase-Angle vs Frequency

### PACKAGE DIMENSIONS

SOT-23 (TO-236AB) CASE 318-08 **ISSUE AN** 



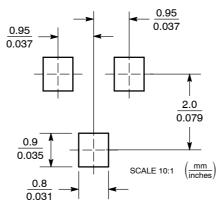
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
He	2 10	2.40	2.64	0.003	0.004	0.104

STYLE 10:

- PIN 1. DRAIN 2. SOURCE
  - 3 GATE

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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